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Two of the histograms in Fig. 3 have been accidentally swapped.1 The third histogram (blue bars) represents the height distribution for quantum dots (QDs) capped with InxGa1−xAs, where x = 0.05. The corresponding average height is 3.1 ± 0.4 nm. The second histogram (green bars) represents the height distribution for QD capped with InxGa1−xAs, where x = 0.10. The average height for this distribution is 4.0 ± 0.5 nm.

The correct image is shown below.

FIG. 3. Height distribution for capped QDs. Increasing the In concentration in the InxGa1−xAs capping layer increases the average height of the QDs.


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